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**FDD3672\_F085**  
**N-Channel UltraFET Trench MOSFET**  
**100V, 44A, 28mΩ**

**Features**

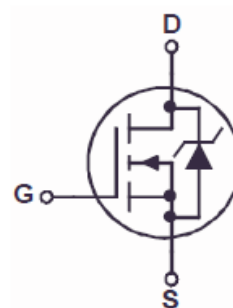
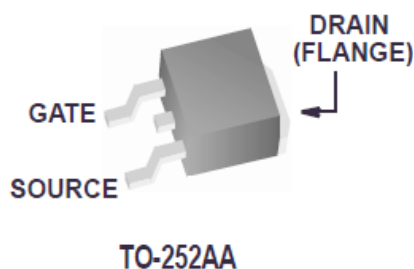
- Typ  $r_{DS(on)}$  = 24mΩ at  $V_{GS} = 10V$ ,  $I_D = 44A$
- Typ  $Q_{g(10)}$  = 24nC at  $V_{GS} = 10V$
- Low Miller Charge
- Low  $Q_{rr}$  Body Diode
- Optimized efficiency at high frequencies
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant

**Applications**

- DC/DC converters and Off-Line UPS
- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier



**FDD3672\_F085 N-Channel UltraFET Trench MOSFET**



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain to Source Voltage	100	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current Continuous ( $T_C < 30^\circ\text{C}$ , $V_{GS} = 10\text{V}$ )	44	A
	Pulsed	See Figure 4	
$E_{AS}$	Single Pulse Avalanche Energy (Note 1)	73	mJ
$P_D$	Power Dissipation	144	W
	Derate above $25^\circ\text{C}$	0.96	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature	-55 to +175	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Maximum Thermal Resistance Junction to Case	1.04	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Maximum Thermal Resistance Junction to Ambient TO-263, 1in <sup>2</sup> copper pad area	52	$^\circ\text{C}/\text{W}$

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD3672	FDD3672_F085	TO-252AA	330mm	16mm	2500 units

### Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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#### Off Characteristics

$B_{VDSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	100	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{V}$ , $V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
		$T_J = 150^\circ\text{C}$	-	-	250	
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA

#### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	2	3	4	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 44\text{A}$ , $V_{GS} = 10\text{V}$	-	0.024	0.028	$\Omega$
		$I_D = 21\text{A}$ , $V_{GS} = 6\text{V}$	-	0.028	0.047	$\Omega$
		$I_D = 44\text{A}$ , $V_{GS} = 10\text{V}$ , $T_J = 175^\circ\text{C}$	-	0.063	0.074	$\Omega$

#### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$	-	1635	-	pF	
$C_{oss}$	Output Capacitance		-	240	-	pF	
$C_{rss}$	Reverse Transfer Capacitance		-	60	-	pF	
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V	$V_{DD} = 50\text{V}$ $I_D = 44\text{A}$ $I_g = 1.0\text{mA}$	-	24	36	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to 2V		-	3	4.5	nC
$Q_{gs}$	Gate to Source Gate Charge			-	8.3	-	nC
$Q_{gs2}$	Gate Charge Threshold to Plateau			-	5.3	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge			-	5.8	-	nC

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Switching Characteristics**

$t_{on}$	Turn-On Time	$V_{DD} = 50\text{V}, I_D = 44\text{A},$ $V_{GS} = 10\text{V}, R_{GS} = 11\Omega$	-	-	78	ns
$t_{d(on)}$	Turn-On Delay Time		-	12	-	ns
$t_r$	Turn-On Rise Time		-	37	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	24	-	ns
$t_f$	Turn-Off Fall Time		-	44	-	ns
$t_{off}$	Turn-Off Time		-	-	70	ns

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Voltage	$I_{SD} = 44\text{A}$	-	0.9	1.25	V
		$I_{SD} = 21\text{A}$	-	0.8	1.0	V
$t_{rr}$	Reverse Recovery Time	$I_F = 44\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	44	57	ns
$Q_{rr}$	Reverse Recovery Charge		-	58	76	nC

**Notes:**

1: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.2\text{mH}$ ,  $I_{AS} = 27\text{A}$

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: <http://www.aecouncil.com/>  
 All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

**Typical Characteristics**

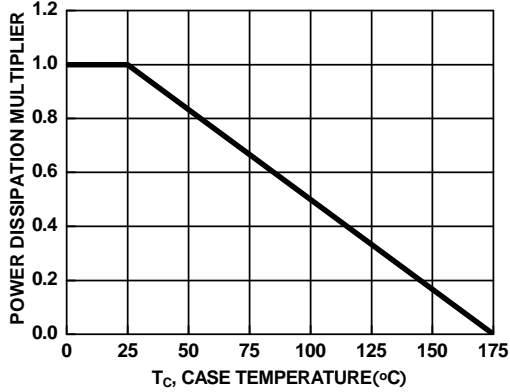


Figure 1. Normalized Power Dissipation vs Case Temperature

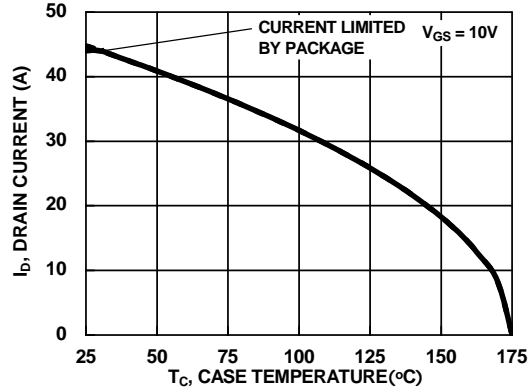


Figure 2. Maximum Continuous Drain Current vs Case Temperature

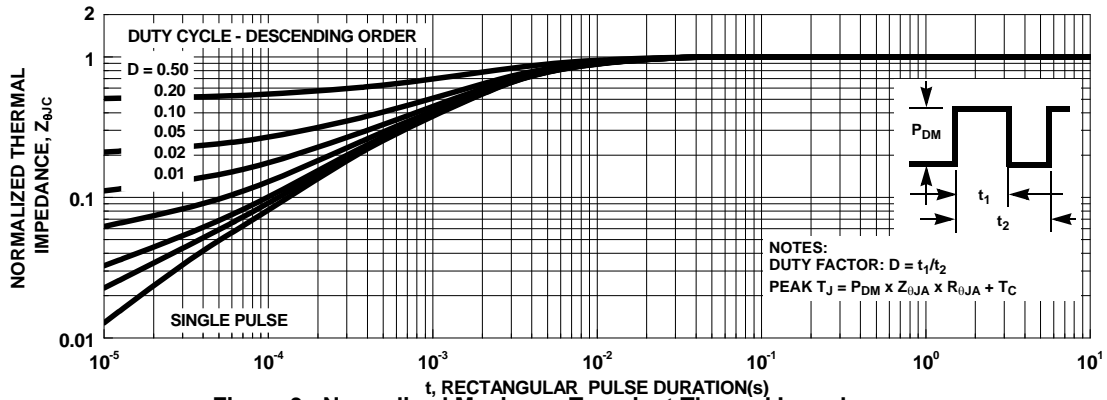


Figure 3. Normalized Maximum Transient Thermal Impedance

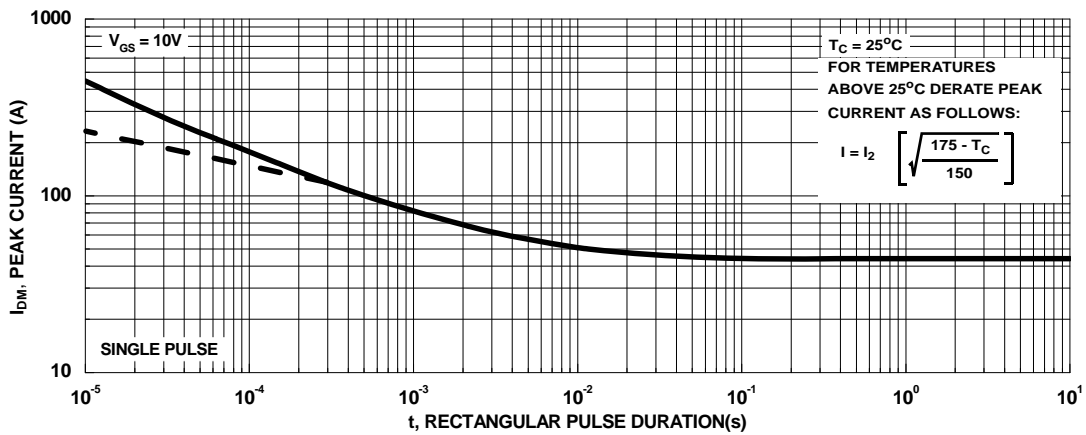


Figure 4. Peak Current Capability

**Typical Characteristics**

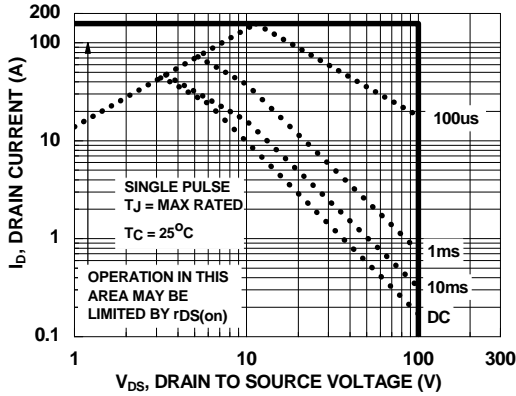
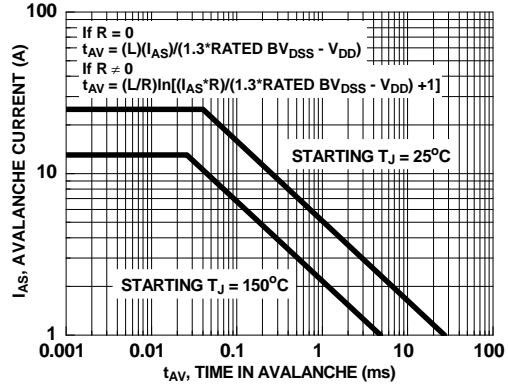


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515  
 Figure 6. Unclamped Inductive Switching Capability

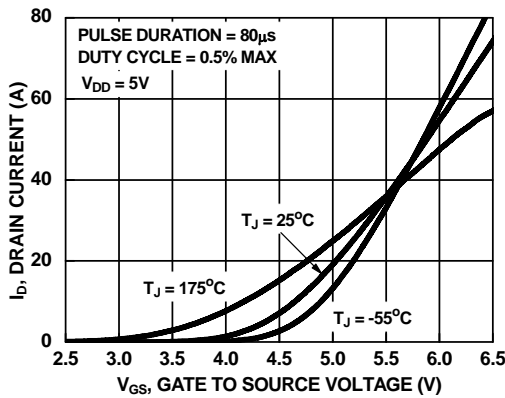


Figure 7. Transfer Characteristics

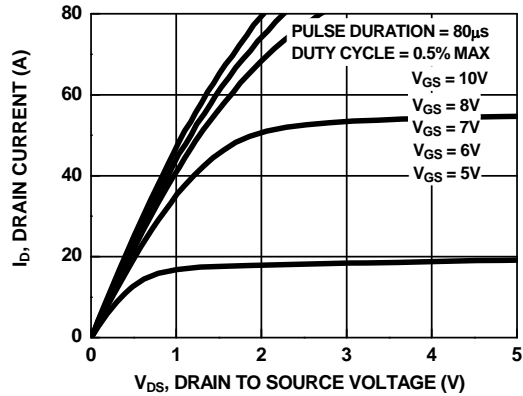


Figure 8. Saturation Characteristics

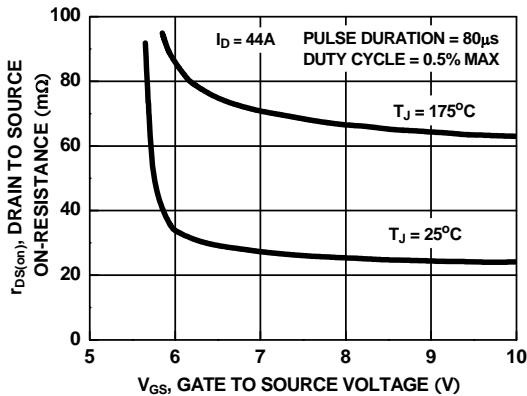


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

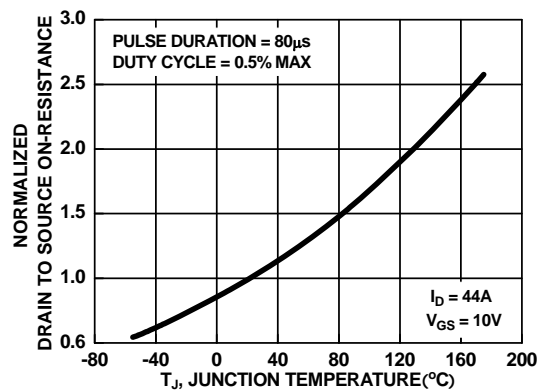


Figure 10. Normalized Drain to Source On-Resistance vs Junction Temperature

**Typical Characteristics**

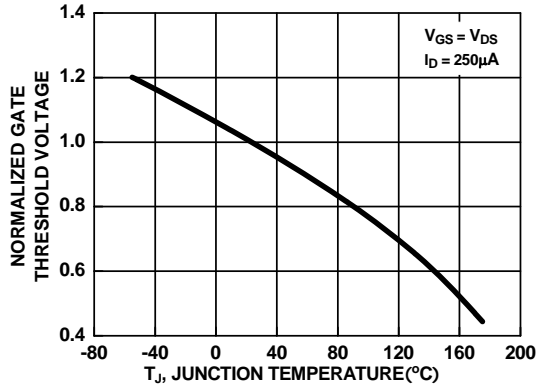


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

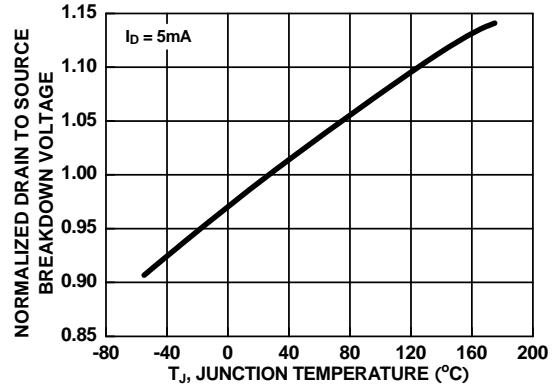


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

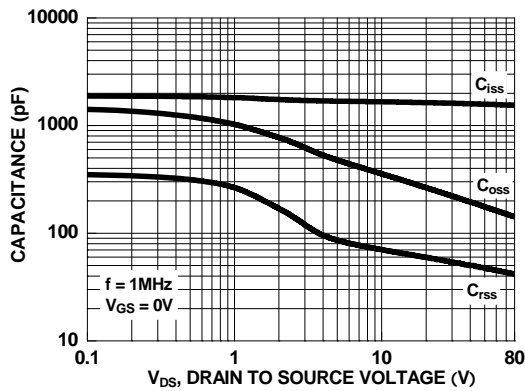


Figure 13. Capacitance vs Drain to Source Voltage

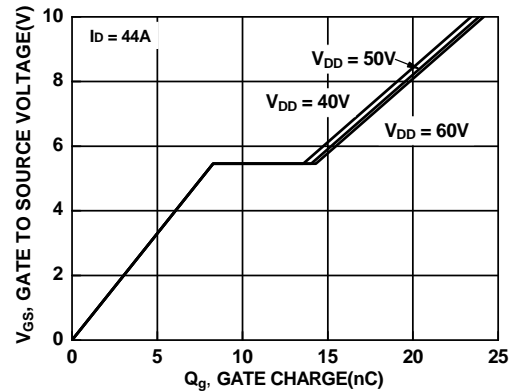


Figure 14. Gate Charge vs Gate to Source Voltage